

 **Insulated Gate Bipolar Transistor**

Features

- ▶ Low voltage drop at high currents
- ▶ Industry standard TO-252 (D-Pak) package
- ▶ 700V breakdown voltage rating

Applications

- ▶ White goods
- ▶ Small appliances
- ▶ Lighting controls
- ▶ Motor drives
- ▶ Meter readers
- ▶ Small off-line power supplies

General Description

The Supertex GN2470 is a 700V, 3.5amp insulated gate bipolar transistor (IGBT) that combines the positive aspects of both BJTs and MOSFETs.

The GN2470 IGBT has lower on-state voltage drop with high blocking voltage capabilities and features many desirable properties including a MOS input gate, low conduction voltage drop at high currents.

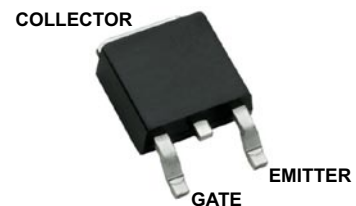
Ordering Information

Device	Package Option
	TO-252 (D-PAK)
GN2470	GN2470K4-G

-G indicates that the package is RoHS certified ("Green")

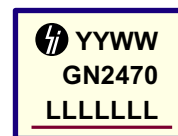


Pin Configuration



TO-252 (D-PAK) (K4)

Pin Configuration



YY = Year Sealed
 WW = Week Sealed
 L = Lot Number
 _____ = "Green" Packaging

TO-252 (D-PAK) (K4)

Absolute Maximum Ratings

Parameter	Value
Collector-to-emitter voltage	700V
Gate-to-emitter voltage	±20V
Operating junction and storage temperature range	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* Distance of 1.6mm from case for 10 seconds.

Thermal Characteristics

Package	I_C (continuous)	I_C (pulsed)	Power Dissipation @ $T_A = 25^\circ\text{C}$	θ_{jc} ($^\circ\text{C}/\text{W}$)	θ_{ja} ($^\circ\text{C}/\text{W}$)
TO-252	1.0A	3.5A	2.5W	10	60†

Notes:

† Mounted on FR4 board, 25mm x 25mm x 1.57mm

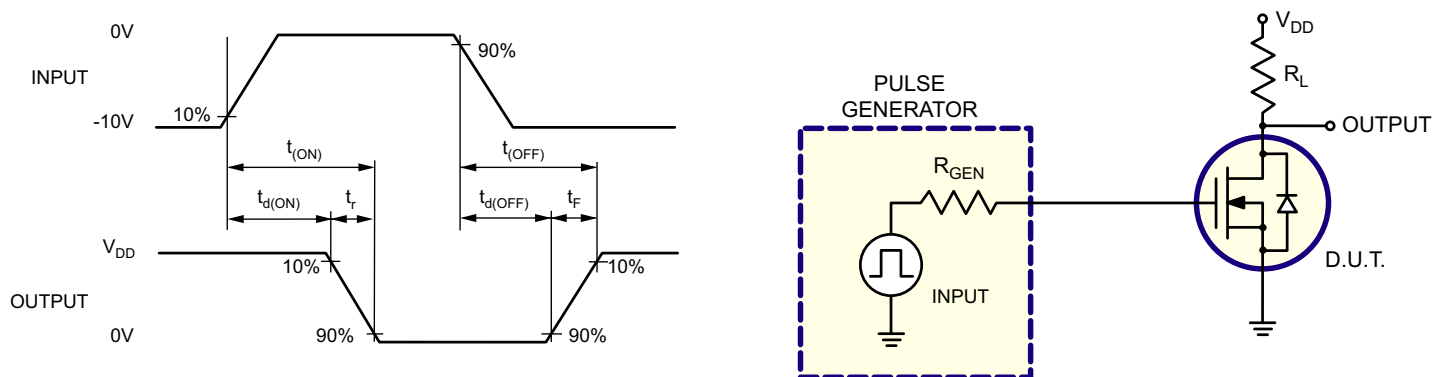
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{CES}	Collector-to-emitter breakdown voltage	700	-	-	V	$V_{GE} = 0\text{V}, I_C = 250\mu\text{A}$
BV_{ECS}	Emitter-to-collector breakdown voltage	-6.0	-10	-	V	$V_{GE} = 0\text{V}, I_C = 1.0\text{mA}$
$V_{GE(th)}$	Gate threshold voltage	1.5	-	3.5	V	$V_{CE} = V_{GE}, I_C = 1.0\text{mA}$
V_{CE}	Collector-to-emitter voltage drop	-	4.5	5.0	V	$I_C = 3.0\text{A}, V_{GE} = 13\text{V}$
g_{fe}	Forward transconductance	0.5	0.8	-	mho	$V_{CE} = 25\text{V}, I_C = 2.0\text{A}$
I_{CES}	Zero gate voltage collector current	-	-	100	μA	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$
I_{GES}	Gate-to-emitter leakage current	-	-	± 100	nA	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$
$I_{C(ON)}$	On-state collector current	3.0	4.0	-	A	$V_{GE} = 10\text{V}, V_{CE} = 25\text{V}$
$t_{d(ON)}$	Turn-on delay time	-	8.0	15	ns	$V_{CC} = 25\text{V}$ $R_{GEN} = 25\Omega$ $R_L = 11\Omega$
t_r	Rise time	-	400	600		
$t_{d(OFF)}$	Turn-off delay time	-	20	50		
t_f	Fall time	-	7000	12000		
C_{ISS}	Input capacitance	-	100	150	pF	$V_{CE} = 25\text{V}$ $V_{GE} = 0\text{V}$ $f = 1\text{MHz}$
C_{OSS}	Output capacitance	-	12	25		
C_{RSS}	Reverse transfer capacitance	-	2	5		

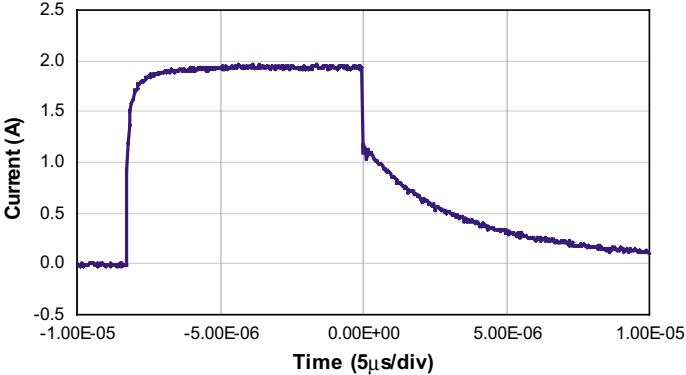
Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

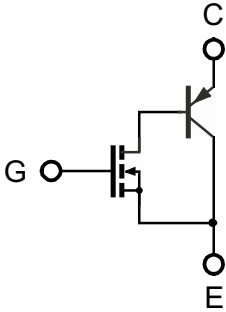
Switching Waveforms and Test Circuit



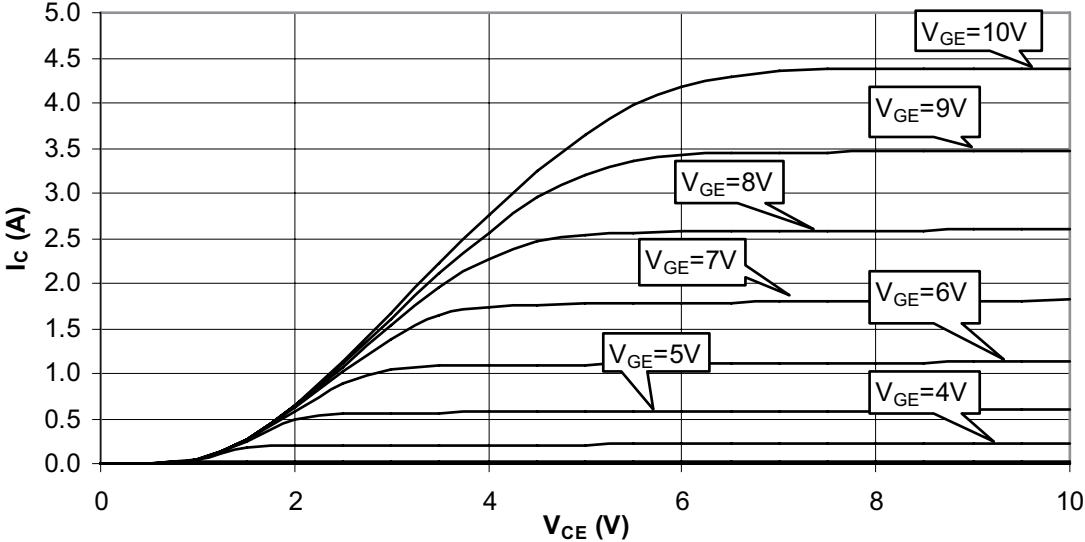
Typical Performance Waveform



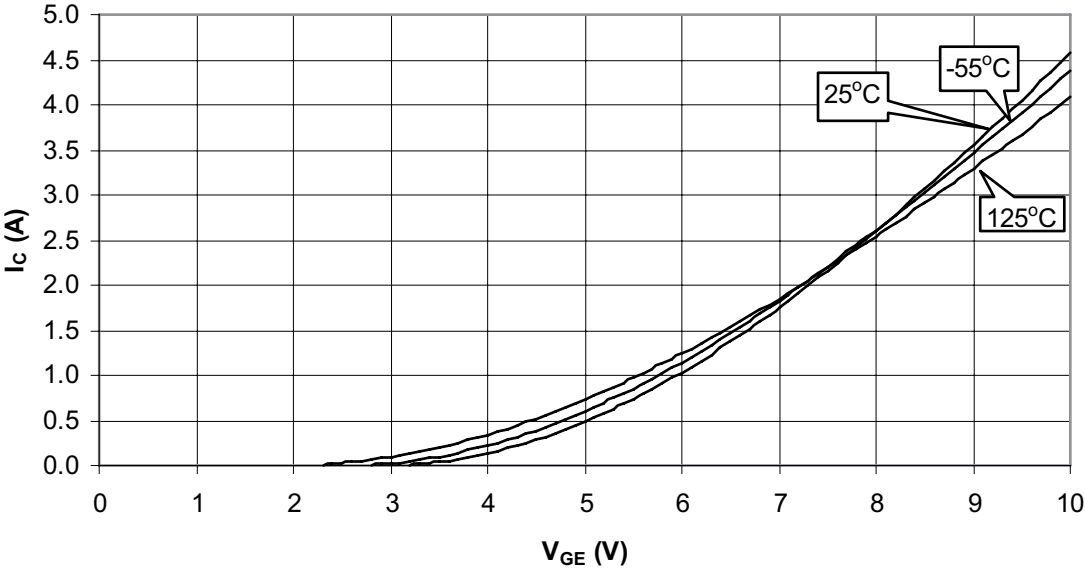
Equivalent Circuit



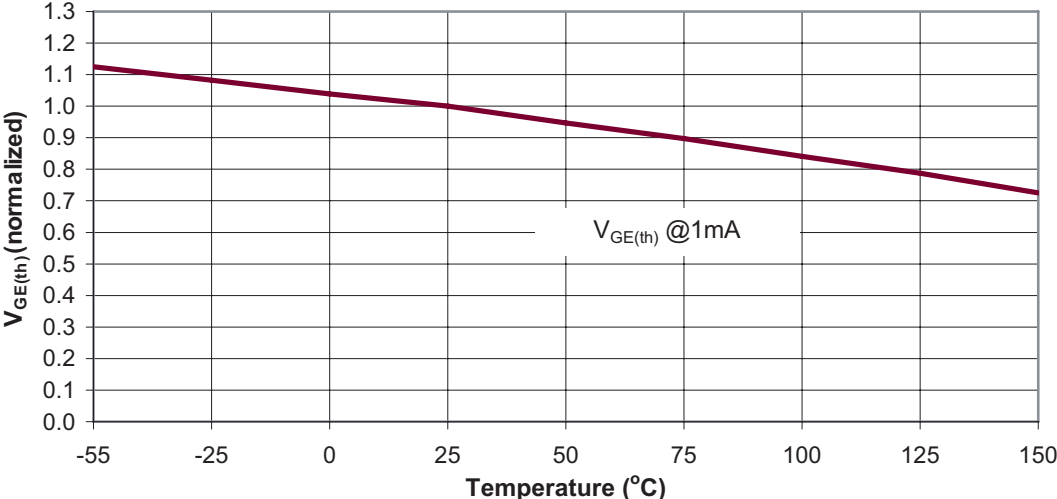
Saturation Characteristics



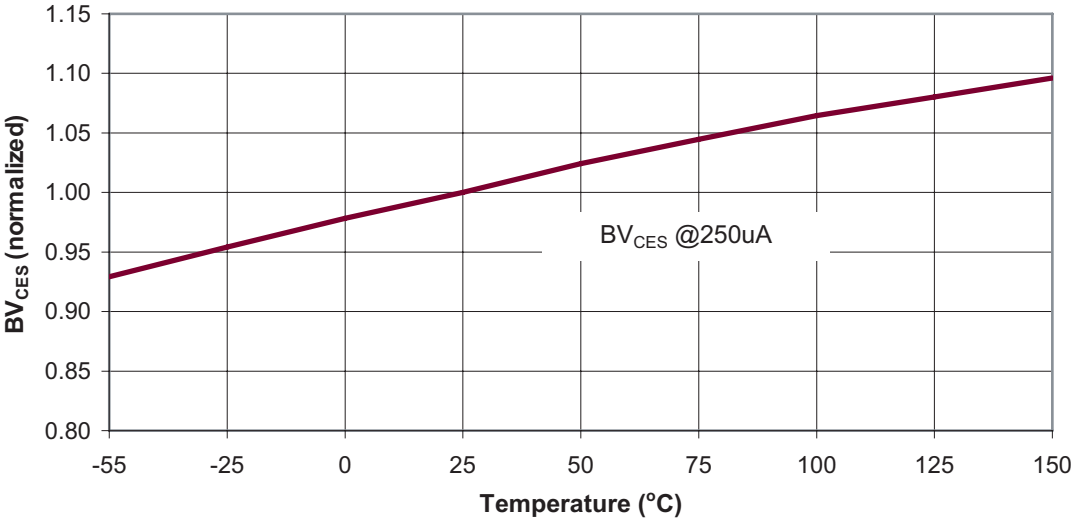
Transfer Characteristics



$V_{GE(th)}$ Variation with Temperature



BV_{CES} Variation with Temperature



Transconductance vs. Collector Current

